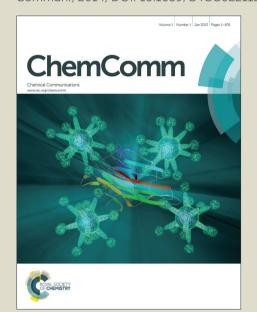
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Mesoscopic TiO₂/CH₃NH₃PbI₃ perovskite solar cells with new hole-transporting materials containing butadiene derivatives

Received 00th January 2012, Accepted 00th January 2012

DOI: 10.1039/x0xx00000x

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Two new triphenylamine-based hole-transporting materials (HTMs) containing butadiene derivatives are employed in CH₃NH₃PbI₃ perovskite solar cells. Up to 11.63% of power conversion efficiency (PCE) has been achieved. Advantages of easy synthesis, low cost and relatively good cell performance exhibit a possibility for commercial application in the future.

Organolead halide perovskites have attracted lots of interests due to their outstanding advantages of direct band gap, large absorption coefficient and high carrier mobility.^{1,2} In 2009, T. Miyasaka pioneered organolead halide perovskites as sensitizers in liquid-type sensitized solar cells with power conversion efficiencies (PCEs) of 3.13% for CH₃NH₃PbBr₃ and 3.81% for CH₃NH₃PbI₃, which was further improved to 6.5% by N.-G. Park. 3,4 Over the last two years, solid-state organolead halide perovskite thin film solar cells developed rapidly, and unexpected breakthrough has been achieved.^{5,6} It is expected that the perovskite solar cell is comparable to conventional thin film solar cells (Cu(In,Ga)Se2, CdTe). Currently, perovskite solar cells with and without hole-transporting materials (HTMs) have been developing. The perovskite solar cells without HTMs exhibited a PCE over 10%, whereas the corresponding devices with HTMs can exhibit much higher efficiencies, over 16% so far.8 The use of HTMs is often perceived to impart some advantages to the cells, mainly facilitating the hole transport to metal anode and blocking the electron transfer from perovskites to metal

Different HTMs have already been demonstrated to work well in perovskite solar cells. First, a few polymer HTMs were successfully applied in this kind of solar cells, such as poly(3-hexylthiophene) (P3HT), poly-triarylamine (PTAA), poly[2,1,3-benzothiadiazole-4,7-diyl[4,4-bis(2-ethylhexyl)-4H-cyclopenta[2,1-b:3,4-b']dithiophene-2,6-diyl]] (PCPDTBT) and so on. P12 Typically, the perovskite solar cells with PTAA exhibited 12% of PCE. Moreover, low molecular weight amorphous HTMs are also good candidates due to their easy purification and good film-forming property simply processed by coating technique. Based on state of the art *spiro*-OMeTAD (2,2',7,7'-tetrakis[N,N-di-p-methoxyphenylamine]-9,9'-spirobi fluorene) as the HTM, M. Gräzel, H. J. Snaith And T. L. Kelly bottained over 15% of PCEs by using different mesoporous scaffolds

or planar heterojunction structures, respectively. And CH₃NH₃PbI₃ perovskite solar cells with pyrene arylamine derivatives presented 12.4% of PCE. ¹⁶ Besides organic HTMs, inorganic hole conductor like CuI with higher conductivity in the perovskite solar cells was also explored, achieving 6% of PCE. ¹⁷ However, current HTMs for this kind of solar cells suffer from high cost or unsatisfactory cell performance, both of which are disadvantageous for future commercialization. Therefore, it is urgent to develop new HTMs for stable, highly efficient and cost-effective perovskite solar cells.

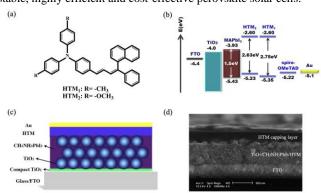


Fig. 1 (a) Molecular structures of HTMs; (b) Energy level diagram of perovskite solar cells with three HTM materials; (c) Device configuration of the perovskite solar cells; (d) Cross-sectional SEM image of FTO/TiO₂/CH₃NH₃PbI₃/HTM₂ film (120 mg mL⁻¹ HTM₂ chlorobenzene solution).

Suitable HTMs for perovskite solar cells should primarily meet following requirements: (1) good hole mobility; (2) compatible HOMO energy level relative to organolead halide perovskite and (3) low cost for commercialization. The triphenylamine entities with butadiene derivatives are known as high hole mobility and good film-forming property, which were applied in organic photo conductors (OPCs). Is In this respect, two new triphenylamine-based hole conductors containing butadiene derivatives have been used in CH₃NH₃PbI₃ perovskite solar cells for the first time, which are 4-(4-phenyl-4-α-naphthylbutadienyl)-N,N-di(4-tolyl)-phenylamine (denoted as

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HTM₁), and 4-(4-phenyl-4-α-naphthylbutadienyl)-N,N-di(4-methoxyphenyl)-phenylamine (denoted as HTM₂), respectively, as shown in Fig. 1(a). Under AM1.5 irradiation (100 mW cm⁻²), the PECs of 11.63% for HTM₂ and 11.34% for HTM₁ have been achieved, in comparison with the PCE for the cell with *spiro*-OMeTAD (12.08%). Our preliminary results reveal that both HTM₁ and HTM₂ are promising alternatives to *spiro*-OMeTAD. And they are quite cheap for potential commercialization.

HTM₁ and HTM₂ were synthesized from Wittig-Horner reaction, which detailed procedures for the syntheses and characterization can be found in our previous work. 18 Their maximum absorption bands are located in the visible region, which are 451 nm for HTM1 and 471 nm for HTM₂, respectively. At room temperature, their hole transporting mobilities are evaluated by time-of-flight (TOF) transient hole-current measurement, which are 2.98×10⁻³ for HTM₁ and 1.27×10^{-3} cm² V⁻¹ S⁻¹ for HTM₂, respectively. The energy levels of HTM₁ and HTM₂ are determined by ultraviolet photoelectron spectroscopy (UPS) and cyclic voltammetry (CV) measurements, as shown in Fig. 1(b). It is thus deduced that different p-position substituents (electron-donating ability -OCH₃>-CH₃) on phenyl rings of the triphenylamine part do not strongly influence their energy levels since triphenylamine and butadiene derivatives form a large π conjugated system. Moreover, both HTMs have suitable HOMO level in comparison to the valence band of CH₃NH₃PbI₃ (-5.43 eV), suggesting good HTMs for CH₃NH₃PbI₃ perovskite solar cells.

For fabricating the device (see Fig. 1(c)), 50 nm-thickness TiO₂ compact layer and 400 nm-thickness mesoporous TiO₂ anatase layer were deposited on FTO glass in sequence according to the literature. 5 CH₃NH₃PbI₃ was subsequently deposited on the mesoporous TiO2 film by using a sequential method as reported. 13 HTMs with proper concentrations were spin-coated on the mesoporous TiO₂/CH₃NH₃PbI₃ film at 3000 rpm for 20s, and an 80 nm-thickness Au layer was finally deposited on the top of the HTM layer by thermal evaporation. For comparison, the device with spiro-OMeTAD was also fabricated by the same condition. Fig. 1(d) shows the cross-sectional scanning electron microscopy (SEM, FEI, XL30 S-FEG) image of FTO/TiO₂/CH₃NH₃PbI₃/HTM₂ film with 120 mg mL⁻¹ HTM solution. We can see that CH₃NH₃PbI₃ is evenly distributed in TiO₂ mesoscopic pores. And 271 nm-thickness HTM₂ capping layer is observed whereas no obvious capping layer when using 20 mg mL⁻¹ HTM₂.

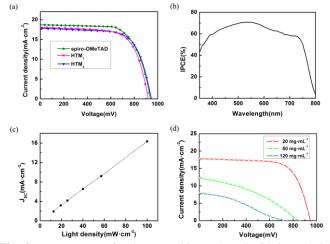


Fig. 2 (a) *J-V* curves for the perovskite solar cells fabricated with HTM₁, HTM₂ and *spiro*-OMeTAD; (b) IPCE spectrum of the cell with HTM₂. The concentration of the HTMs: 20 mg mL⁻¹ solution in

chlorobenzene; (c) Plot of the J_{sc} of CH₃NH₃PbI₃ perovskite solar cells with HTM₂ vs. light densities; (d) J-V curves for the perovskite solar cells with different HTM₂ concentration.

Fig. 2(a) shows photocurrent density-photovoltage (J-V) curves of three cells with different HTMs. All of the three HTM films were obtained from 20 mg mL⁻¹ solution in chlorobenzene. We can see that, when new HTMs are introduced into the device, the PCEs are 11.34% for HTM₁ with short-circuit photocurrent density (J_{sc}) of 18.1 mA cm⁻², open-circuit photovoltage (V_{oc}) of 921 mV and fill factor (FF) of 0.68 and 11.63% for HTM₂ with J_{sc} of 17.9 mA cm⁻², V_{oc} of 942 mV and FF of 0.69, respectively. These are comparative to that of spiro-OMeTAD-based perovskite solar cells under the same fabrication method, which photovoltaic parameters are J_{sc} of 18.7 mA cm⁻², V_{oc} of 936 mV, and FF of 0.69, yielding 12.08% of PCE, in agreement with those reported by S. I. Seok. ¹⁹ The V_{oc} of the devices with HTM2 and spiro-OMeTAD are close, in agreement with their similar HOMO levels since the theoretical V_{oc} is determined by the difference in the quasi-Fermi levels of the electrons in the TiO_2 and the holes in the HTM. However, the V_{oc} of the HTM₁-based device is slightly lower, which is abnormal since its HOMO level is relatively lower, see Table. S1. The origin of this phenomenon is still not fully understood so far, however, the dependence of the V_{oc} on the HTMs is also influenced by charge recombination kinetics. ¹⁶ The monochromatic incident photon-toelectron conversion efficiency (IPCE) spectrum of the cell with HTM₂ is presented in Fig. 2(b).²⁰ An integral photocurrent from the overlap of the IPCE spectrum is 15.8 mA cm⁻², basically in agreement with the experimentally obtained J_{sc} . Besides, the above result further confirms that the two substituents (-CH₃ and -OCH₃) do not strongly influence their HOMO levels and the cell performance. So, we will take HTM₂ as an example to further investigate the properties of the cell in the following discussion.

The dependence of J_{sc} of the device with HTM₂ on light densities is also investigated. As shown in Fig. 2(c), the J_{sc} is linearly proportional to light density, indicating that the charge collection efficiency in the device is independent with light intensities. According to previous investigation, it is suggested that no space-charge limit exists in the TiO₂/CH₃NH₃PbI₃/HTM₂ junction due to small difference in the mobility between electrons and holes.^{5,21}

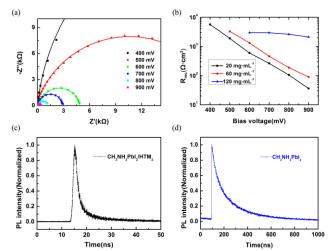


Fig. 3 (a) Nyquist plots of the device with thin layer HTM₂ in the dark over different forward biases, scattered point: experimental data, solid line: fitted curves; (b) Plots of recombination resistance (R_{rec}) vs bias voltages for the devices with different thickness HTM₂; (c) and (d) PL intensities for CH₃NH₃PbI₃/HTM₂ and CH₃NH₃PbI₃

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films, respectively, monitored at 775 nm during the transformation. Excitation at 445 nm.

In order to investigate the influence of HTM_2 deposition amount on the cell performance, a series of perovskite solar cells were fabricated by varying spin coating concentration. As shown in Fig. 2(d), with the HTM spin coating concentration increasing, HTM_2 overlayer is getting thicker from unclear to 271 nm, however, the cell performance is getting poorer. At higher concentration, the increasing capping layer thickness will increase the series resistance and cause the FF decreased by nearly 50%. The decrease of V_{oc} is mainly due to the dark current augments with the HTM film thickness increasing, lowering the electron concentration as well as their Fermi level. It is thus deduced that, thin HTM layer will facilitate the hole transport as well as the cell performance. Further improvement in the conductivity of the HTM layer as well as the cell performance will be carried out in the future.

To understand the thickness-related influence on the cell performance, electrochemical impedance spectroscopy (EIS) was carried out, in which the potential bias was applied from 400 to 900 mV in the dark in the frequency range from 10⁵ to 0.1 Hz (Zahner IM6ex), as shown in Fig. 3(a). According to simplified transmission line model, the main arc is supposed to be the combination of the recombination resistance (R_{rec}) and the chemical capacitance of the film (CPE_{μ}), see Fig. S1. ^{17,22-23} By fitting the Nyquist plots, the relationship between the R_{rec} and the bias voltage is obtained.⁵ From Fig. 3(b), we can see that (1) for the same device, R_{rec} drops with the increasing forward bias voltage, mainly because the Fermi level in the mesoscopic TiO₂ is elevated under the forward bias (> 500 mV) which is beneficial to easy electron flow across TiO₂/CH₃NH₃PbI₃ interface; (2) at the same forward bias voltage, with the thickness of HTM increasing, the R_{rec} increases greatly in all bias voltage ranges, indicating thick capping layer is disadvantageous to the charge transfer. Likewise, large R_{rec} will lead to unsatisfactory cell performance, in good agreement with our test result in Fig. 2(d). Furthermore, time-resolved photoluminescence (PL) decay

measurement has been used to research charge transfer at a stable well-defined interface, as shown in Fig. 3(c) and (d). The PL decay time can be obtained after fitting the data with bi-exponential decay function.²⁴ The TiO₂/CH₃NH₃PbI₃ film exhibits a time constant of τ =195.6 ns. Further introduction of the HTM₂ as a quenching layer remarkably facilitates the PL decay with the time constant τ =1.36 ns. This is due to the diffusion of the photogenerated excitons to the CH₃NH₃PbI₃/HTM₂ interface where they are quenched. It is thus suggested that the existence of CH3NH3PbI3/HTM2 interface is beneficial to the hole transfer and HTM2 has excellent hole pumping capacity as well.^{25, 26} Finally, the device efficiencies from a batch of ten devices using HTM2 under the same conditions are given in Fig. S2. We can see that all of them show a PCE over 11% with an average PCE of 11.30%, indicating their good reproducibility. Preliminary stability test has been carried out, that is, unsealed cells were kept in the dark at ambient conditions which were tested every day during 7 days. The cells with HTM₁ and HTM₂ were quite stable, which PCEs are almost constant with 0.2% drop for HTM₁ and 0.9% drop for HTM₂ comparable to their initial PCEs.

Conclusions

In conclusion, we have, for the first time, employed two new triphenylamine-based HTMs containing butadiene derivatives in CH₃NH₃PbI₃ perovskite solar cells. Both of them show excellent capacity to hole transport, and up to 11.63% of efficiency has been achieved for the CH₃NH₃PbI₃ perovskite solar cell with HTM₂. Their typical advantages are easy synthesis, low cost and relatively good

cell performance, which may provide a possibility for commercial application of organolead halide perovskite solar cells in the future.

The authors would like to thank the financial support from the MOST (973 projects, No. 2012CB932903 and 2012CB932904), Beijing Science and Technology Committee (No. Z131100006013003), NSFC (No. 51072221 and 21173260) and the Knowledge Innovation Program of the Chinese Academy of Sciences.

Notes and references

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